

Contents

Part I Machine Aspects of Ion Implantation

<i>Ion Implantation System Concepts. By H. Glawischnig (With 12 Figures)</i>	3
1. Implanter Concepts	3
1.1 Post-Analysis	3
1.2 Pre-Analysis	3
1.3 Post-Analysis with Post-Acceleration	4
2. Criteria for the Ideal Semiconductor-Manufacturing Implanter	4
3. Low-Current and Medium-Current Implanter Concepts	5
4. High-Current Implanter Concepts	8
5. System-Limiting Aspects	11
5.1 Throughput	11
5.2 Wafer Heating	13
5.3 Energy Range	15
5.4 Wafer Size and Wafer Tilting	15
5.5 Charge-up Phenomena	16
5.6 Contamination	16
6. Human Engineering	18
6.1 Operation of an Implanter	18
6.2 Automatic Implantation Control	18
6.3 Safety	20
References	20
 <i>Ion Sources. By D. Aitken (With 24 Figures)</i>	23
1. Introduction	23
2. Ion Implantation Requirements from the Ion Source	24
3. The Principle of Operation of an Ion Source	24
3.1 The Cathode	25
3.2 The Anode	26
3.3 The Extraction Aperture	27
3.4 The Magnetic Field	27
3.5 The Plasma	28
3.6 The Source Feed System	30
4. Beam Extraction	30
5. Beam Formation	32
6. Beam Quality	34
7. Beam Content	35
8. Ion Source Selection	37
8.1 Low-Current Machines	37
8.2 Medium-Current Machines	37
8.3 High-Current Machines	38
8.4 Surface Treatment Machines	38

9. Types of Arc Discharge Source	39
9.1 Calutron Sources	39
9.2 Magnetron Ion Sources	40
9.3 Penning Ion Source	41
9.4 Plasmatron Ion Sources	43
9.5 Hollow Cathode Sources	44
9.6 Sputtering Sources	45
9.7 Sources for the Surface Treatment of Metals	46
9.8 Other Sources	46
10. Sources Not Utilising an Arc Discharge	49
10.1 Surface Ionisation Sources	49
10.2 Molten Metal Field Emission Ion Sources	50
11. Operational Characteristics of Arc Discharge Sources	51
11.1 Arc Voltage	52
11.2 Arc Current	53
11.3 Magnetic Field Strength	54
11.4 Arc Chamber Pressure	54
11.5 Feed Material	55
11.6 Temperature	55
11.7 Source Condition	56
11.8 Extraction Voltage	56
12. Ion Source Feed Materials	57
12.1 Gaseous Feed Materials	57
12.2 Low Vapour Pressure Materials	57
12.3 Very Low Vapour Pressure Materials	58
12.4 Chemical Synthesis	58
12.5 Feed Materials	59
13. Materials of Construction	59
13.1 Arc Chamber Materials	59
13.2 Cathode Materials	64
13.3 Insulator Materials	65
13.4 Magnetic Materials	65
13.5 Electrical Conductors	65
13.6 Coating Materials	65
14. Ion Sources in Commercial Ion Implanters	65
14.1 Sources for Low-Current Machines	66
14.2 Medium-Current Machines	67
14.3 High-Current Machines	67
15. Conclusions	70
References	70

Faraday Cup Designs for Ion Implantation

By Ch.M. McKenna (With 23 Figures)	73
1. Introduction	73
2. Dose Control by Current Measurement	73
2.1 Assumptions	73
2.2 Discrepancies	74
3. Limitations in Dose Measurements with Faraday Cups	75
3.1 Ion Beam Space-Charge Effects	76
3.2 Secondary and Tertiary Particle Emissions in the Faraday Cup..	79
3.3 Target Area Effects	83
3.4 Electrical Errors	84
4. Design Principles for Faraday Cups	85
5. Faraday Cup Design for Dose Measurement for Scanned Beams	85
5.1 Beam Space Charge and Secondary Particle Collection	85
5.2 Implant Area	88
5.3 Electrical Considerations	89

6. Faraday Cup Design for Dose Measurement for Scanned Targets	90
6.1 Beam Space Charge, Surface Neutralization and Secondary Particle Collection	90
6.2 Implant Area	96
6.3 Electrical Considerations	96
7. In Situ Monitoring of Dose Uniformity	97
7.1 Uniformity Control for Scanned Beams	97
7.2 Uniformity Control for Scanned Targets	99
8. Hybrid Systems	100
9. Summary	101
References	101

Safety and Ion Implanters

By R. Bustin and P.H. Rose (With 10 Figures)	105
1. Radiation	105
1.1 Mechanisms of X-Ray Production	105
1.2 X-Ray Production Efficiency	106
1.3 Generation of the Reverse Electron Flow Responsible for X-Ray Production	107
1.4 Mechanisms of X-Ray Absorption	108
1.5 Radiation Units	111
1.6 Example of a Radiation-Level Calculation	112
2. Poisonous Materials	113
3. High Voltage	116
4. Mechanical Hazards	118
5. Fire, Flooding, Earthquake	119
5.1 Fire	119
5.2 Flooding	119
5.3 Earthquake	120
References	120

Part II Ion Ranges in Solids

The Stopping and Range of Ions in Solids

By J.P. Biersack and J.F. Ziegler (With 22 Figures)	122
1. Introduction	122
2. Review of Some Stopping and Range Tables	124
2.1 Stopping Power Tables	125
2.2 Range Tables	138
3. Stopping Powers for Ions in Solids	145
3.1 Nuclear Stopping Powers	145
3.2 The Electronic Stopping of Ions in Solids	150
3.3 Empirical Ion Stopping Powers	151
References	155

The Calculation of Ion Ranges in Solids with Analytic Solutions

By J.P. Biersack and J.F. Ziegler (With 4 Figures)	157
1. Introduction	157
2. The Basic Ideas of the Model	157
2.1 Directional Spread of Ion Motion During the Slowing-Down Process	157
2.2 Connection Between Angular Spread Parameter τ and Energy Loss	159
2.3 Calculation of the Mean Projected Range	160

3. Application of the Model	160
3.1 Heavy-Ion Ranges as an Example of Possible Analytic Treatment	160
3.2 Differential Equation and Universal Algorithm for Projected Ranges	162
3.3 Universal Analytic Approximation for Projected Ranges	164
4. Projected Ranges in Compound Targets	166
5. Higher Terms and Precision	167
6. Appendix	167
6.1 Numerical Evaluation of Projected Ranges on Programmable Pocket Calculators (PRAL)	167
6.2 Numerical Evaluation of Projected Ranges on Computers (DIMUS)	169
References	170

<i>Range Distributions</i> . By H. Ryssel (With 18 Figures)	177
1. Introduction	177
2. Gaussian Profiles	177
3. Pearson Distributions	179
4. Other Distributions	183
5. Two-Layer Targets	184
6. Implantation and Sputtering	187
7. Lateral Spread	190
8. Appendix: Range Program	194
References	205

Part III Measuring Techniques and Annealing

<i>Electrical Measuring Techniques</i> . By P.L.F. Hemment (With 17 Figures)	209
1. Introduction	209
2. Background	209
2.1 Why Post-Implantation Dosimetry	209
2.2 Incident and Retained Dose	210
2.3 Absolute and Relative Dose Measurement	211
2.4 Sample Contamination	212
2.5 Post-Implantation Annealing	212
2.6 Basic Assumptions	212
3. Measurement Techniques	213
3.1 Resistance Measurements	213
3.2 Capacitance Voltage	222
3.3 Device Parameters	223
3.4 Depth Profiles	226
4. Limitations of Electrical Measurements	228
5. Standards Exercises	231
References	232

Wafer Mapping Techniques for Characterization of Ion Implantation Processing

By M.I. Current, D.S. Perloff, and L.S. Gutai (With 22 Figures)	235
1. Introduction	235
2. High-Dose Characterization: Sheet Resistance Measurements	236
2.1 The van der Pauw Resistor	237
2.2 The Four-Point Probe	237
3. Sheet Resistance Wafer Mapping	239
3.1 Performance Norms for Dose Accuracy and Uniformity	239

3.2	Implanter Diagnostics	241
3.3	Effects of Annealing Conditions	245
3.4	Wafer Heating During Implantation	247
4.	Low-Dose Characterization	249
4.1	Device Parameters	249
4.2	High-Frequency Capacitance Technique	251
5.	Summary	253
	References	254

Non-Electrical Measuring Techniques

By P. Eichinger and H. Ryssel (With 41 Figures)		255
1.	Introduction	255
2.	Structure of Implantation-Related Analytical Problems	256
3.	Review of Measurement Techniques: Impurity Profiling	258
3.1	Abrasive Techniques	258
3.2	Non-Destructive Methods	265
4.	Secondary Ion Mass Spectroscopy (SIMS)	275
4.1	Sputtering and Secondary Ionization	276
4.2	Experimental Techniques	280
5.	Rutherford Backscattering (RBS)	285
5.1	Concepts of RBS	286
5.2	Experimental Technique	289
6.	Damage Evaluation by Channeling Techniques	290
6.1	Channeling of Energetic Light Ions	291
6.2	Channeling Spectra and Lattice Disorder	293
6.3	Lattice Location	296
	References	296

<i>Annealing and Residual Damage.</i> By S. Mader (With 16 Figures)		299
1.	Introduction	299
2.	Characterization of Damage and Defects	300
3.	Primary Implantation Damage	301
4.	Thermal Annealing	302
5.	Residual Defects	305
6.	Effects of Residual Defects	311
	References	314

Part IV Appendix: Modern Ion Implantation Equipment

Evolution and Performance of the Nova NV-10 PredepTM Implanter

By G. Ryding (With 24 Figures)		319
1.	Introduction	319
2.	Performance Specifications	319
3.	Dose Control	319
4.	Throughput	324
4.1	Implant Time	324
4.2	The Wafer Handling Sequence Between Implants	325
4.3	Throughput Values	325
5.	Uptime	326
6.	Beam Current and Source Performance	327
7.	Energy	329
8.	Wafer Cooling	330
8.1	Uncooled Disks	331
8.2	Radiation-Enhanced Cooling	331
8.3	2-Point Clamp Technique	331
8.4	Full-Ring Centrifugal Clamp	332

9. Preventive Maintenance	332
10. Process Control (DataLock™)	334
11. Neutral Beams	337
11.1 Dose Error	338
11.2 Dose Non-uniformity	338
11.3 Depth Profile Errors	339
11.4 Secondary Particle Effects	340
12. Contamination	340
13. Wafer Handling	340
14. Summary	341
References	342

Ion Implantation Equipment from Veeco

By W.A. Scaife and K. Westphal (With 5 Figures)	343
1. Introduction	343
2. A Versatile Ion Implantation System	343
3. A High-Production Ion Implantation System	347
4. Ion Implanter for GaAs - Device Development and Production	348

<i>The Series IIIA and IIIX Ion Implanters.</i> By D. Aitken (With 7 Figures).	351
1. Introduction	351
2. The Series III Machine	351
3. The Series IIIA Machine	353
4. The Series IIIX Machine	355
5. The Electron Flood Gun	356
6. The Process Verification System	356
7. Specifications	357
7.1 IIIA	357
7.2 IIIX	358
References	358

Standard High-Voltage Power Supplies for Ion Implantation

By M. Baumann (With 1 Figure)	359
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The IONMICROPROBE A-DIDA 3000-30 for Dopant Depth Profiling and Impurity Bulk Analysis

By J.L. Maul and H. Frenzel (With 7 Figures)	361
1. Introduction	361
2. Some Features of the IONMICROPROBE A-DIDA 3000-30	361
3. Some IONMICROPROBE A-DIDA 3000-30 Applications	365
References	366

<i>List of Contributors</i>	367
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<i>Subject Index</i>	369
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